

Vishay High Power Products

"Half-Bridge" IGBT INT-A-PAK (Standard Speed IGBT), 200 A

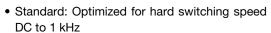


INT-A-PAK

PRODUCT SUMMARY					
V _{CES}	600 V				
I _C DC	480 A				
V _{CE(on)} at 200 A, 25 °C	1.13 V				

FEATURES

• Generation 4 IGBT technology





- Very low conduction losses
- Industry standard package
- UL approved file E78996
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level

BENEFITS

- · Increased operating efficiency
- · Direct mounting to heatsink
- Performance optimized as output inverter stage for TIG welding machines

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Collector to emitter voltage	V _{CES}		600	V	
Continuous collector current	,	T _C = 25 °C	480		
	IC	T _C = 116 °C	200	•	
Pulsed collector current	I _{CM}		800	A	
Peak switching current	I _{LM}		800		
Gate to emitter voltage	V _{GE}		± 20	V	
RMS isolation voltage	V _{ISOL}	Any terminal to case, t = 1 minute	2500	V	
Maximum power dissipation	В	T _C = 25 °C	830	14/	
	P_{D}	T _C = 85 °C	430	W	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Collector to emitter breakdown voltage	V _{BR(CES)}	$V_{GE} = 0 \text{ V}, I_C = 1 \text{ mA}$	600	-	-		
Collector to emitter voltage	V _{CE(on)}	V _{GE} = 15 V, I _C = 200 A	-	1.13	1.21	V	
		$V_{GE} = 15 \text{ V}, I_{C} = 200 \text{ A}, T_{J} = 125 ^{\circ}\text{C}$	-	1.08	1.18		
Gate threshold voltage	$V_{GE(th)}$	I _C = 0.25 mA	3	4.5	6		
Collector to emitter leakage current	I _{CES}	$V_{GE} = 0 \text{ V}, V_{CE} = 600 \text{ V}$	-	0.025	1	A	
		V _{GE} = 0 V, V _{CE} = 600 V, T _J = 125 °C	-	-	10	mA	
Gate to emitter leakage current	I _{GES}	V _{GE} = ± 20 V	-	-	± 250	nA	

Document Number: 94362 Revision: 03-May-10

GA200HS60S1PbF

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SWITCHING CHARACTERISTICS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Total gate charge	Qg	I _C = 200 A	-	1600	1700	
Gate to emitter charge	Q_{ge}	V _{CC} = 400 V	-	260	340	nC
Gate to collector charge	Q_{gc}	V _{GE} = 15 V	-	580	670	
Turn-on switching loss	E _{on}	I _C = 200 A, V _{CC} = 480 V, V _{GF} = 15 V	-	30	=	
Turn-off switching loss	E _{off}	$R_g = 10 \Omega$	-	50	=	mJ
Total switching loss	E _{ts}	Freewheeling diode: 30EPH06, T _J = 25 °C	-	80	-	
Turn-on switching loss	E _{on}	I _C = 200 A, V _{CC} = 480 V, V _{GF} = 15 V	-	34	=	
Turn-off switching loss	E _{off}	$R_g = 10 \Omega$	-	104	=	mJ
Total switching loss	E _{ts}	Freewheeling diode: 30EPH06, T _J = 125 °C	-	138	151	
Input capacitance	C _{ies}	V _{GF} = 0 V	-	32 500	-	
Output capacitance	C _{oes}	V _{CC} = 30 V	-	2080	-	pF
Reverse transfer capacitance	C _{res}	f = 1.0 MHz	-	380	-	

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNITS	
Operating junction temperature range		T _J	- 40	-	150	°C	
Storage temperature range		T _{Stg}	- 40	-	125		
Junction to case per leg		R _{thJC}	-	-	0.15	°C/W	
Case to sink		R _{thCS}	-	0.1	-	C/VV	
Mounting torque	case to heatsink		-	-	4	- Nm	
	case to terminal 1, 2, 3		-	-	3		
Weight			-	185	-	g	

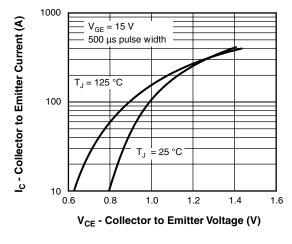


Fig. 1 - Typical Output Characteristics

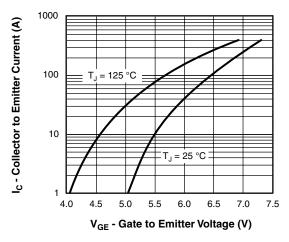


Fig. 2 - Typical Transfer Characteristics





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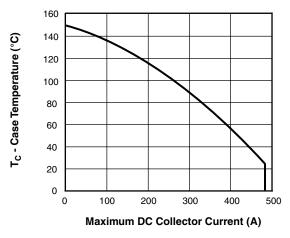


Fig. 3 - Case Temperature vs. Maximum Collector Current

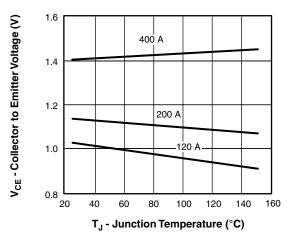


Fig. 4 - Typical Collector to Emitter Voltage vs. Junction Temperature

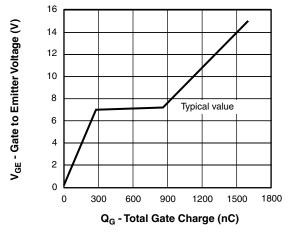


Fig. 5 - Typical Gate Charge vs. Gate to Emitter Voltage

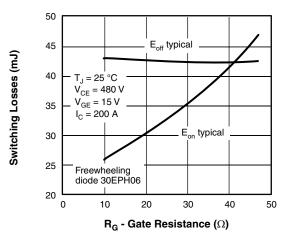


Fig. 6 - Typical Switching Losses vs. Gate Resistance

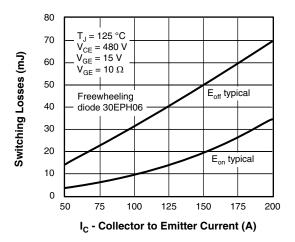
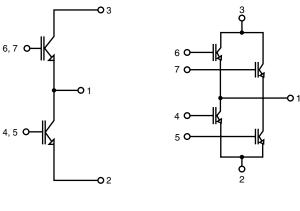


Fig. 7 - Typical Switching Losses vs. Collector to Emitter Current



Functional Diagram Electrical Diagram

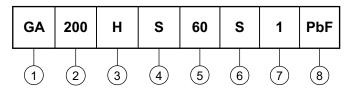
GA200HS60S1PbF

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ORDERING INFORMATION TABLE

Device code



1 - Essential part number IGBT modules

2 - Current rating (200 = 200 A)

Circuit configuration (H = Half bridge without f/w diode)

4 - INT-A-PAK

5 - Voltage code (60 = 600 V)

6 - Speed/type (S = Standard speed IGBT)

Assy location ItalyPbF = Lead (Pb)-free

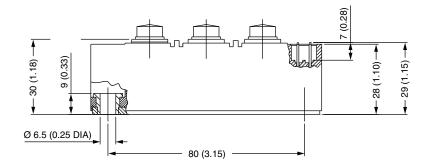
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95067			

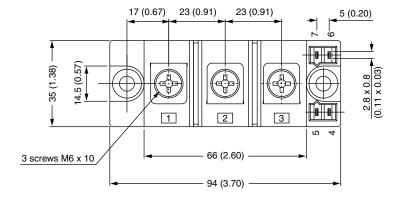


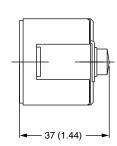
Vishay Semiconductors

INT-A-PAK IGBT/Thyristor

DIMENSIONS in millimeters (inches)











Vishay

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Revision: 11-Mar-11